

FIG. 1

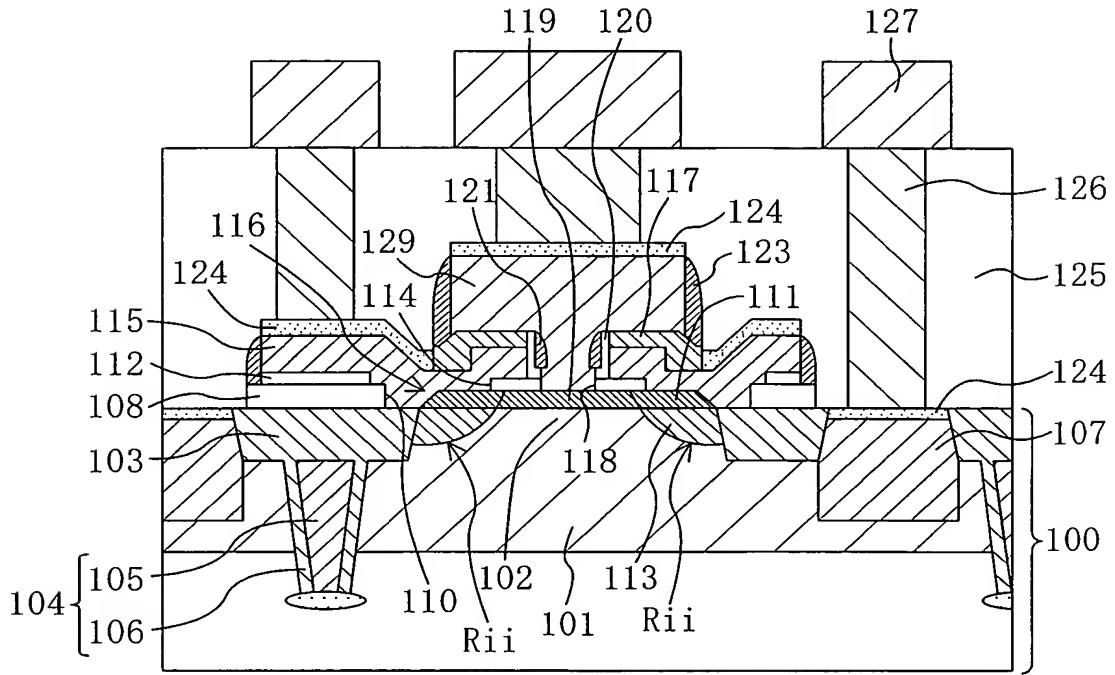


FIG. 2(a)

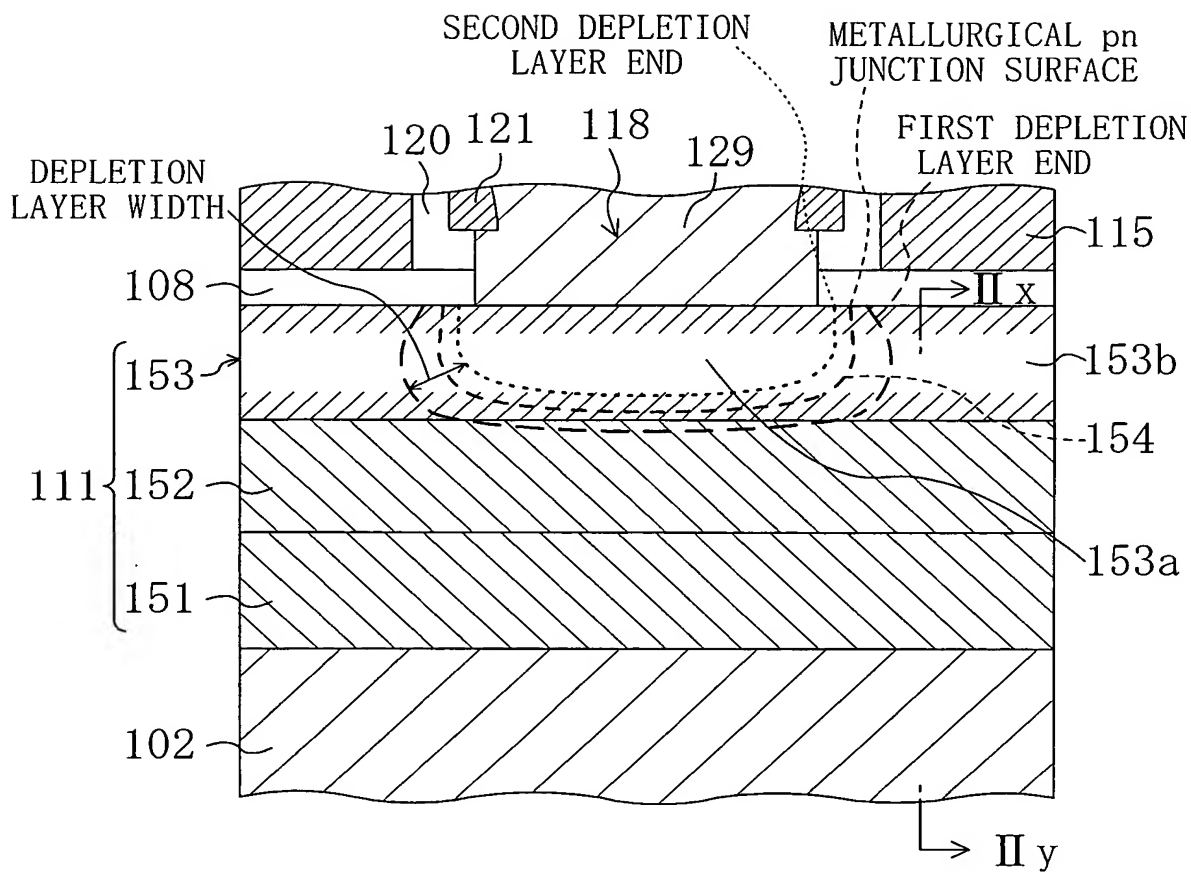
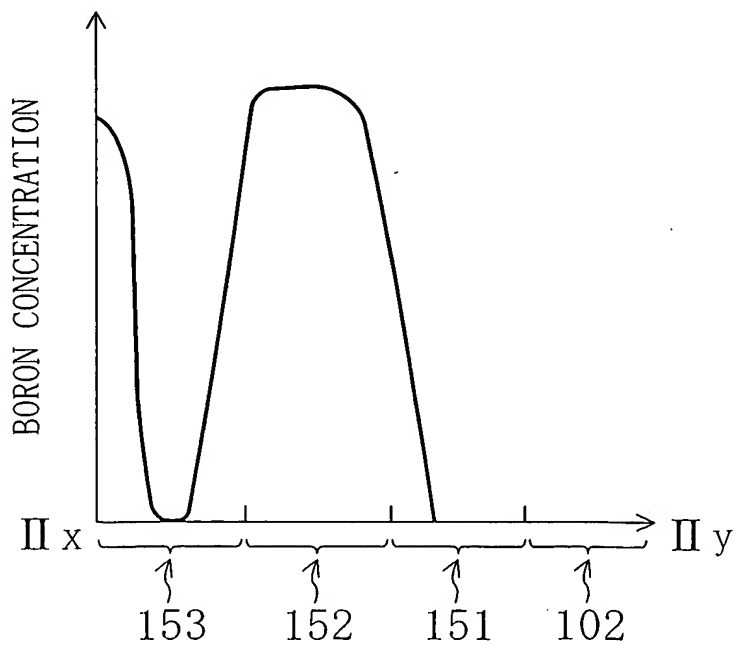


FIG. 2(b)



A cross-sectional view of a semiconductor device 100. The device includes a substrate 101 with a patterned layer 102 on its top surface. A top layer 103 is formed on the patterned layer 102. A central structure 104 is formed in the substrate 101, consisting of a core 105 and a base 106. Side structures 107 are also formed in the substrate 101, adjacent to the central structure 104.

[illegible][illegible]

[illegible][illegible]

FIG. 7 (a)

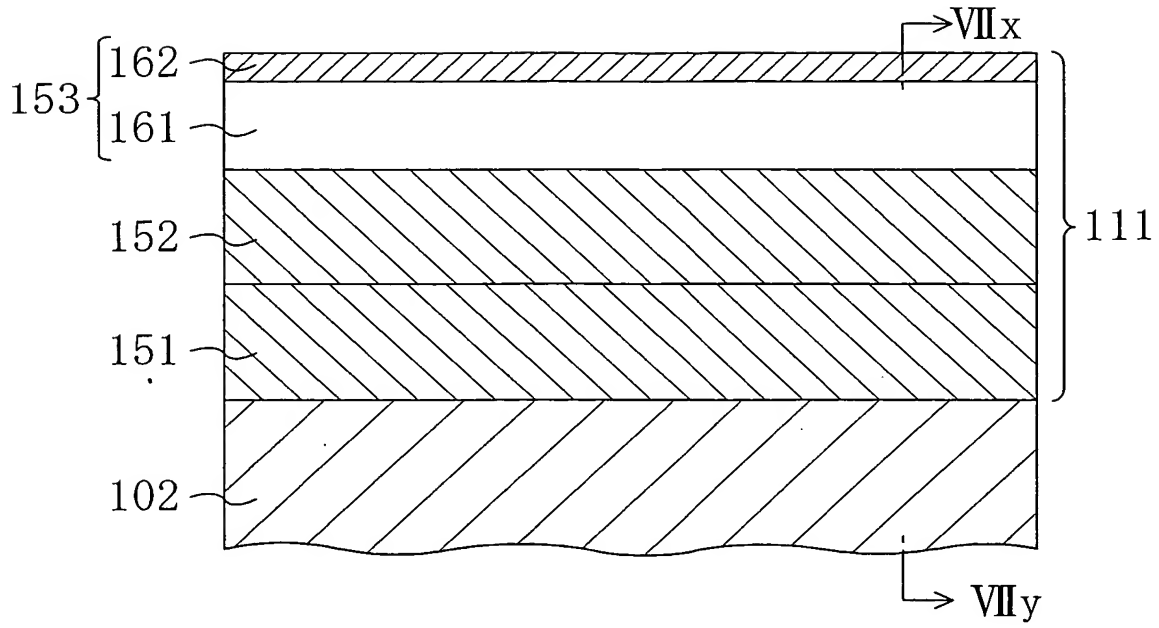


FIG. 7 (b)

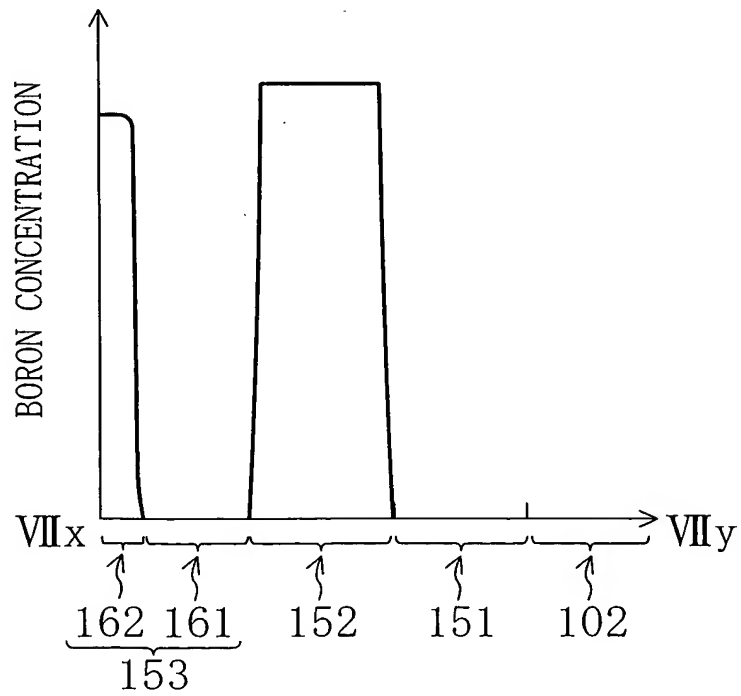


FIG. 8(a)

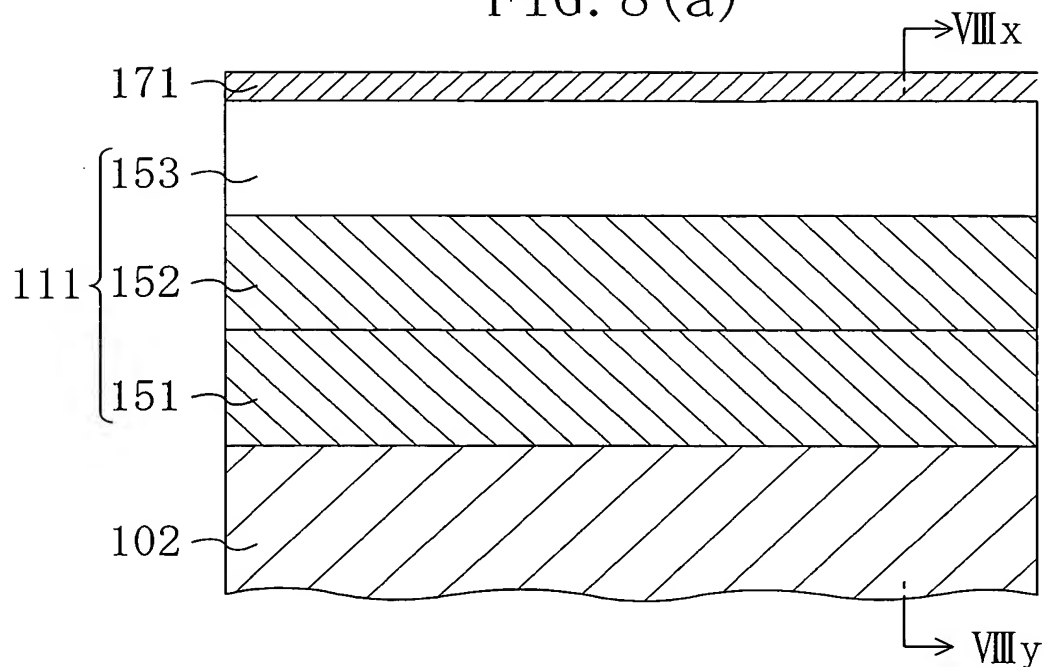
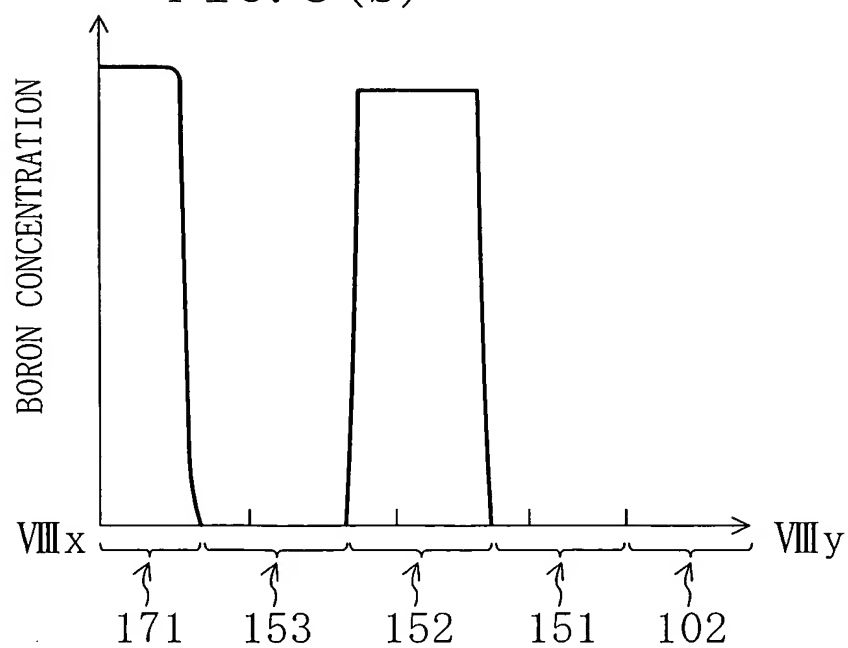


FIG. 8(b)



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FIG. 9(a)

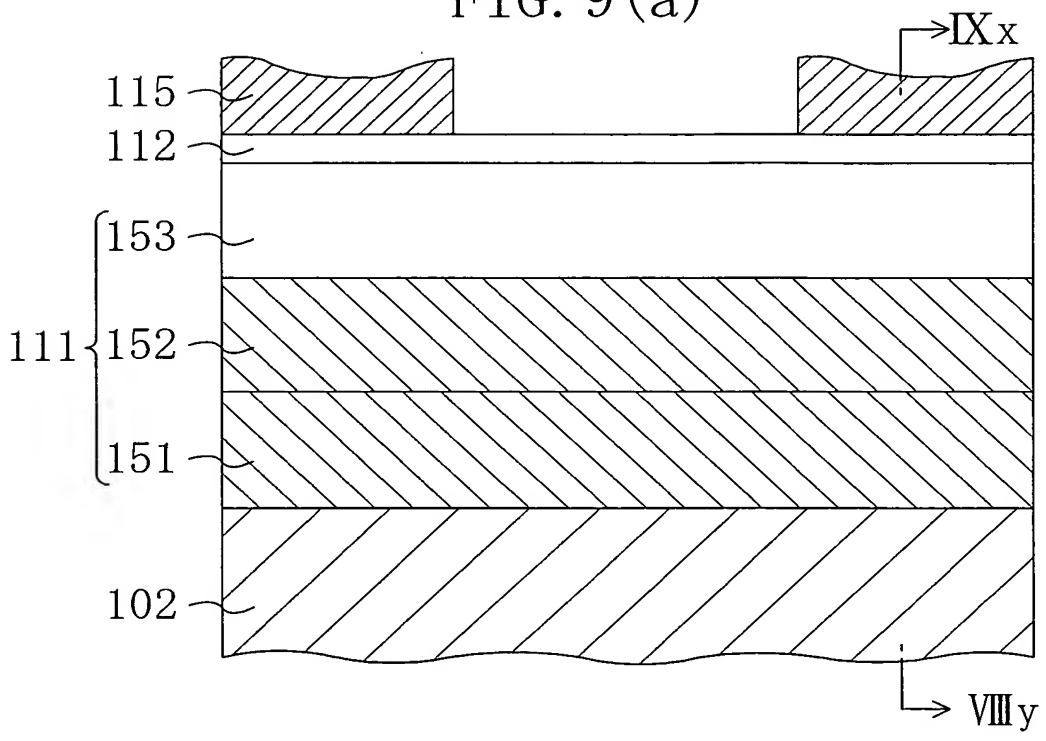


FIG. 9(b)

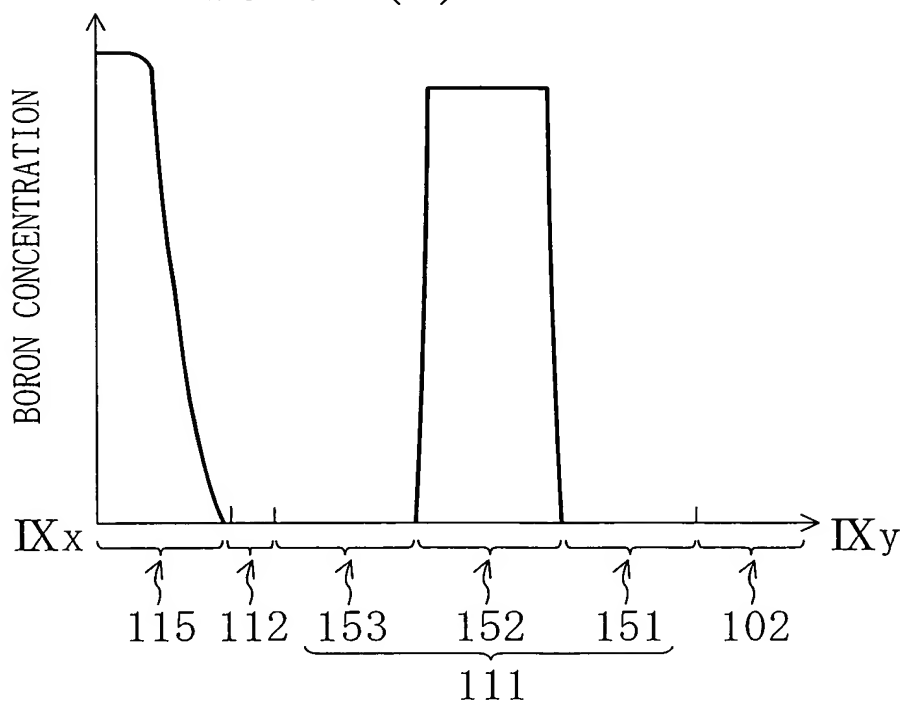


FIG. 11 (a)

BASE CURRENT, COLLECTOR CURRENT (A)

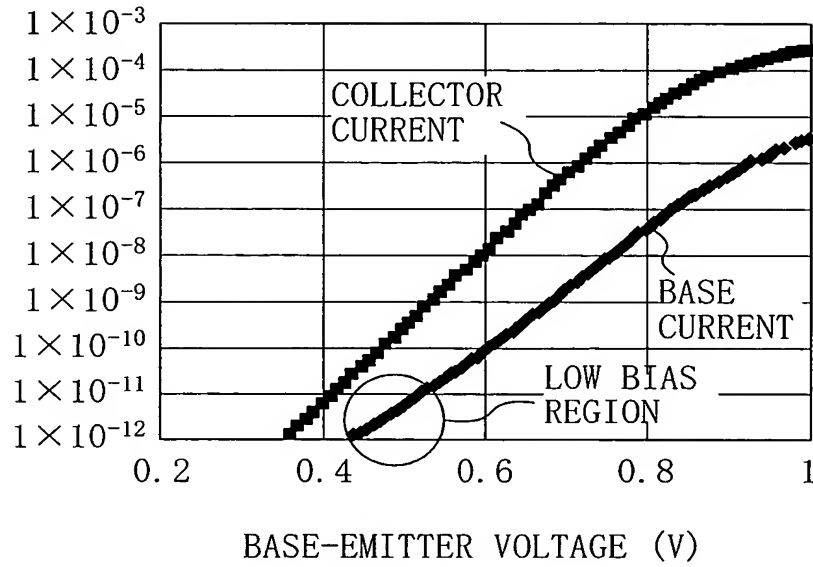


FIG. 11 (b)

BASE CURRENT, COLLECTOR CURRENT (A)

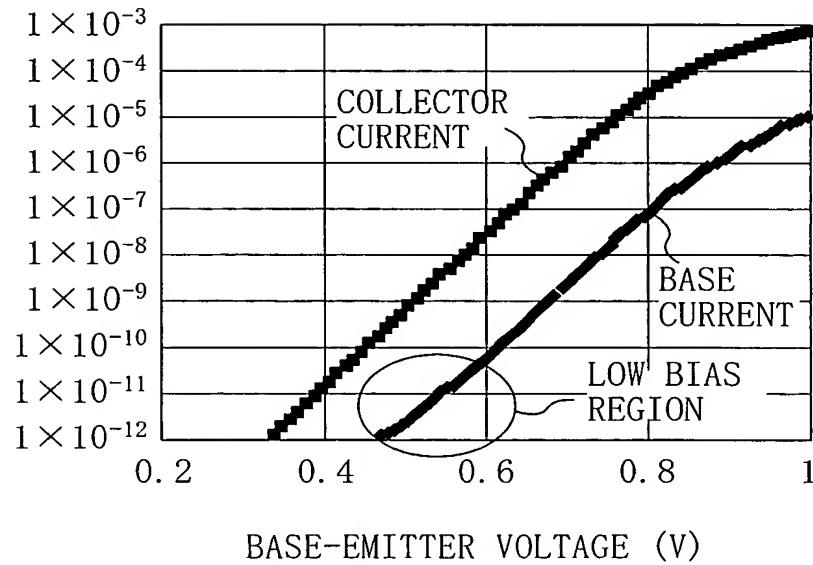


FIG. 12(a)
PRIOR ART

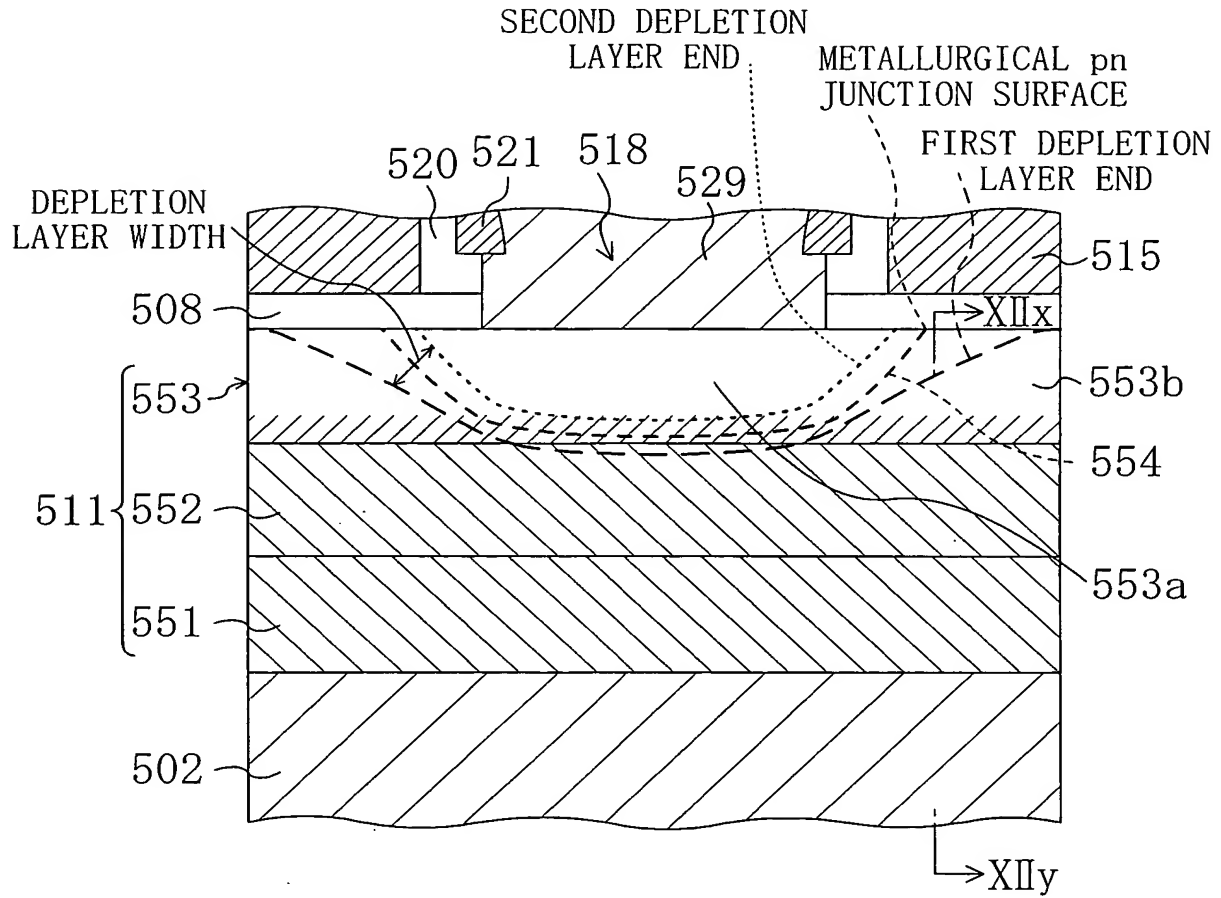
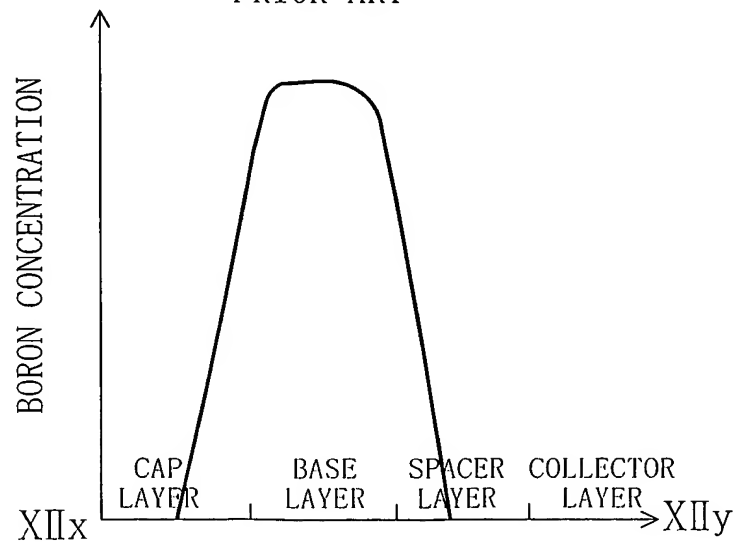


FIG. 12(b)
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